

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
6 January 2005 (06.01.2005)

PCT

(10) International Publication Number
WO 2005/001911 A1

(51) International Patent Classification⁷: **H01L 21/02**

(21) International Application Number:
PCT/KR2004/001533

(22) International Filing Date: 24 June 2004 (24.06.2004)

(25) Filing Language: Korean

(26) Publication Language: English

(30) Priority Data:
10-2003-0042584 27 June 2003 (27.06.2003) KR

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG,
MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH,
PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN,
TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

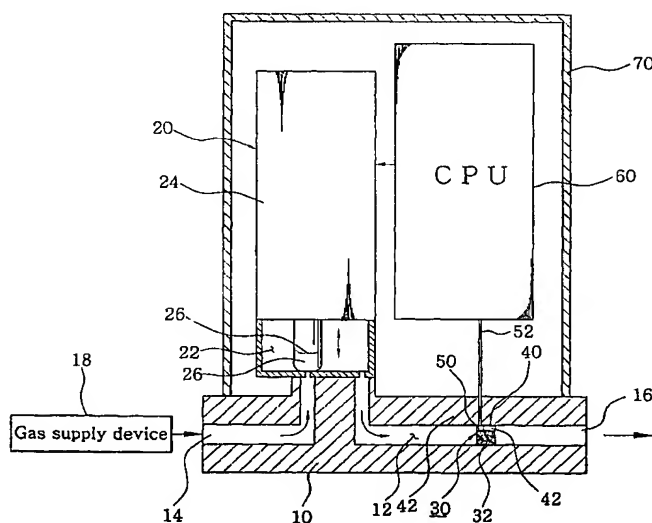
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,
SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: APPARATUS FOR CONTROLLING FLOW RATE OF GASES USED IN SEMICONDUCTOR DEVICE BY DIFFER-
ENCIAL PRESSURE



(57) Abstract: Provided is apparatus for controlling flow rate of gases used in semiconductor device by differential pressure by generating differential pressure in a fluid path. A differential pressure generation element generates pressure difference in the fluid path of gases used in semiconductor device fabrication, a pressure sensor which is installed at a bypass of the fluid path detects the pressure difference, and a central processing unit(CPU) measures and controls a flow rate of the gases, thereby the present invention is capable of controlling the flow rate precisely and rapidly, and enhancing the degree of purity of the gases by the filtering function of the differential pressure generation element itself.